**Amendments to the Claims**:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A thin film transistor, comprising:

a gate electrode having a gate insulation film;

a channel region that extends through the gate insulation film in the gate electrode; and

source drain regions connected to said channel region that are formed against a semiconductor film that is formed on the surface of an insulation substrate, wherein a recombination center which captures carriers is formed in said channel region by part of a crystal semiconductor film having a relatively low degree of crystallization in crystal semiconductor film that forms said channel region.

2. (Previously Presented) The thin film transistor of Claim 1, wherein said recombination center is concentrated adjacent to said drain regions within said channel region.

3. (Previously Presented) The thin film transistor of Claim 2, wherein said recombination center is concentrated in a region, among channel regions, whose distance from the drain regions is equivalent to 1/3 to 1/10 of a channel length.

4. (Previously Presented) The thin film transistor according to Claim 1, wherein a region, in said channel region, in which said recombination center is concentrated has different film thickness compared to other region.

5. (Previously Presented) The thin film transistor according to Claim 1, wherein a region, in said channel region, in which said recombination center is concentrated has different surface positions compared to other regions.

6. (Previously Presented) The thin film transistor of Claim 5, wherein the region, in said channel region, in which said recombination center is concentrated has different surface height positions compared to other regions due to a different thickness of the semiconductor film forming said channel region.

7. (Previously Presented) The thin film transistor of Claim 5, wherein the region, in said channel region, in which said recombination center is concentrated has different surface height positions compared to other regions due to the formation of at least one of indented sections and bulged sections in a lower layer of the semiconductor films forming said channel regions.

8. (Withdrawn) A method for manufacturing a thin film transistor comprising a gate electrode having a gate insulation film, channel regions that extend through a gate insulation film in the gate electrode, and source drain regions connected to said channel regions that are formed against a semiconductor film being formed on a surface of an insulation substrate, wherein a section having a relatively low degree of crystallization is formed within a predetermined region of said semiconductor films by applying laser annealing to said semiconductor films after forming the semiconductor films that form said channel regions.

9. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 8, wherein a section with a relatively low degree of crystallization is formed in the predetermined regions of said semiconductor film by applying said laser annealing to said semiconductor film after forming the semiconductor films with partially different film thickness as semiconductor films that form said channel regions.

10. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 8, wherein a section with a relatively low degree of crystallization is formed in the predetermined regions to said semiconductor film by applying said laser annealing for said

semiconductor film after forming the semiconductor films with different surface height positions as semiconductor films that form said channel regions.

11. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 10, wherein the thickness of said semiconductor film is made to be different partially in forming said semiconductor film with different surface height positions.

12. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 11, wherein at least one of an indented section and a bulging section is formed beforehand in a lower layer of said semiconductor films in forming said semiconductor films with different surface height positions.

13. (Previously Presented) The thin film transistor according to Claim 2, wherein a region, in said channel region, in which said recombination center is concentrated have different film thickness compared to other regions.

14. (Previously Presented) The thin film transistor according to Claim 3, wherein the region, in said channel region, in which said recombination center is concentrated has different film thickness compared to other regions.

15. (Previously Presented) The thin film transistor according to Claim 2, wherein the region, in said channel region, in which said recombination center is concentrated has different surface positions compared to other regions.

16. (Previously Presented) The thin film transistor according to Claim 3, wherein the region, in said channel region, in which said recombination center is concentrated have different surface positions compared to other regions.

17. (Previously Presented) A display device having a thin film transistor, the thin film transistor comprising:

a gate electrode having a gate insulation film;

a channel region that extends through the gate insulation film in the gate electrode; and

source drain regions connected to said channel regions that are formed against a semiconductor film that is formed on the surface of an insulation substrate, wherein a recombination center which capture carriers is formed in said channel region by part of crystal semiconductor films having a relatively low degree of crystallization among crystal semiconductor films that form said channel region.

18. (Withdrawn) A method for manufacturing a display device having a thin-film transistor, the thin-film transistor comprising a:

gate electrode having a gate insulation film, channel regions that extend through a gate insulation film in the gate electrode, and source drain regions connected to said channel regions that are formed against a semiconductor film being formed on a surface of an insulation substrate, wherein a section having a relatively low degree of crystallization is formed within a predetermined region of said semiconductor films by applying laser annealing to said semiconductor films after forming the semiconductor films that form said channel regions.

19. (Canceled)